

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **ASI MRF392** is a Common Emitter Device Designed for Class A , AB and C Amplifier Applications in the 300 - 500 MHz Military Communications Band.

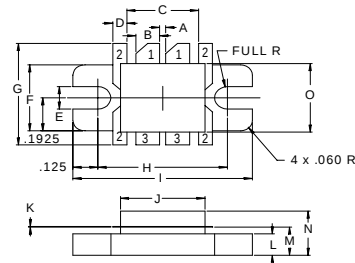
FEATURES INCLUDE:

- Gold Metalization
- Emitter Ballasting
- Input Matching

MAXIMUM RATINGS

I_C	16 A
V_{CB}	60 V
P_{DISS}	270 W @ $T_C = 25^\circ C$
T_J	$-65^\circ C$ to $+200^\circ C$
T_{STG}	$-55^\circ C$ to $+200^\circ C$
θ_{JC}	.65 $^\circ C/W$

PACKAGE STYLE .400 8L FLG



DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.030 / 0.76	
B	.115 / 2.92	.125 / 3.18
C	.360 / 9.14	
D	.065 / 1.65	.075 / 1.91
E	.130 / 3.30	
F	.380 / 9.65	.390 / 9.91
G	.735 / 18.67	.765 / 19.43
H	.645 / 16.38	.655 / 16.64
I	.895 / 22.73	.905 / 22.99
J	.420 / 10.67	.430 / 10.92
K	.003 / 0.08	.007 / 0.18
L	.120 / 3.05	.130 / 3.30
M	.159 / 4.04	.175 / 4.45
N		.280 / 7.11
O	.395 / 10.03	.405 / 10.29

1 = COLLECTOR 2 = EMITTER
3 = BASE

CHARACTERISTICS $T_C = 25^\circ C$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	$I_C = 50$ mA	30			V
BV_{CES}	$I_C = 50$ mA	60			V
BV_{EBO}	$I_E = 5.0$ Ma	4.0			V
I_{CBO}	$V_{CB} = 30$ V			5.0	mA
C_{ob}	$V_{CB} = 28$ V $f = 1.0$ MHz		52		pF
h_{FE}	$V_{CE} = 5.0$ V $I_C = 1.0$ A	20		100	---
G_{pe} η_c	$V_{CE} = 28$ V $P_{out} = 125$ W $f = 400$ MHz	8.0 50	8.5 55		dB %